DMC505E0

Silicon NPN epitaxial planar type

For High frequency amplification DMC205E0 in SMini6 type package

■ Features

- ullet High transition frequency f_T
- Contributes to miniaturization of sets, reduction of component count.
- Eco-friendly Halogen-free package

■ Basic Part Number

Dual DSC2F01X (Common Emitter)

Packaging

MDC505E00R Embossed type (Thermo-compression sealing): 3000 pcs / reel (standard)

■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V_{CBO}	15	V	
Collector-emitter voltage (Base open)	V _{CEO}	10	V	
Emitter-base voltage (Collector open)	V_{EBO}	V _{EBO} 3		
Collector current	I_{C}	50	mA	
Total power dissipation	P_{T}	150	mW	
Junction temperature	T_j	150	°C	
Storage temperature	T _{stg}	-55 to +150	°C	

■ Package

• Code

SMini6-F3-B

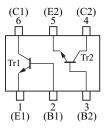
Package dimension clicks here. \rightarrow

• Pin Name

1: Emitter (Tr1) 4: Collector (Tr2) 2: Base (Tr1) 5: Emitter (Tr2) 3: Base (Tr2) 6: Collector (Tr1)

■ Marking Symbol: C8

■ Internal Connection

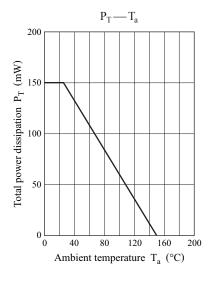


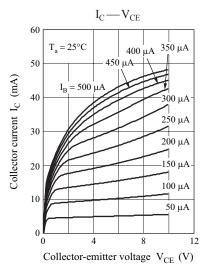
■ Electrical Characteristics $T_a = 25$ °C±3°C

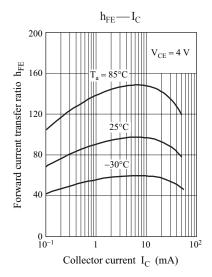
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage (Base open)	V _{CEO}	$I_C = 2 \text{ mA}, I_B = 0$	10			V
Emitter-base voltage (Collector open)	V _{EBO}	$I_E = 10 \mu A, I_C = 0$	3			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 10 \text{ V}, I_{E} = 0$			1	μА
Forward current transfer ratio	h_{FE}	$V_{CE} = 4 \text{ V}, I_{C} = 5 \text{ mA}$	75		220	_
Collector-emitter saturation voltage	V _{CE(sat)}	$I_C = 20 \text{ mA}, I_B = 4 \text{ mA}$			0.5	V
Transition frequency	f_T	$V_{CE} = 4 \text{ V}, I_{C} = 5 \text{ mA}$		1.9		GHz
Collector output capacitance (Common base, input open circuited)	C _{ob}	$V_{CB} = 4 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		1.2		pF
Collector-base parameter	$r_{bb}' \cdot C_C$	$V_{CE} = 4 \text{ V}, I_{C} = 5 \text{ mA}, f = 31.9 \text{ MHz}$		12		ps
Reverse transfer capacitance (Common base)	C _{rb}	$V_{CE} = 4 \text{ V}, I_{C} = 0 \text{ , } f = 1 \text{ MHz}$		0.6		pF

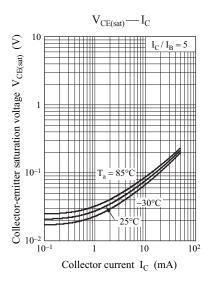
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

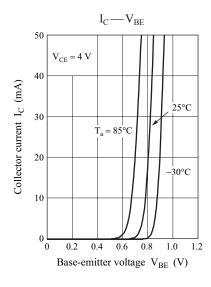
DMC505E0 Panasonic

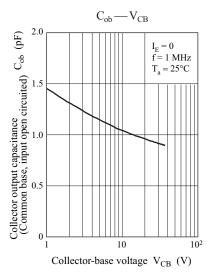


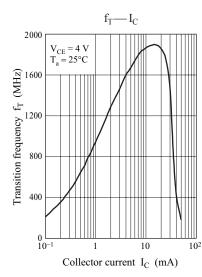












2 Ver. BED

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